

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	)	
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Haihong WANG <i>et al.</i>	)	Group Art Unit: 2826
	)	
Application No.: 10/761,374	)	Examiner: Fazli Erdem
	)	
Filed: January 22, 2004	)	
	)	
For: REVERSED T-SHAPED FINFET	)	

**COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

U.S. Patent and Trademark Office  
Customer Window, Mail Stop: Amendment  
Randolph Building  
401 Dulany Street  
Alexandria, VA 22314

Sir:

In response to the Statement of Reasons for Allowance contained in the Notice of  
Allowance dated March 29, 2007, Applicants submit the following remarks:

**Remarks** begin on page 2 of this paper.

**REMARKS**

Applicants note with appreciation the Examiner's allowance of claims 1-3, 5-11, 17, 19 and 20. Applicants, however, submit the following comments regarding the Examiner's statement of reasons for allowance contained on page 2 of the Notice of Allowance. In the statement of reasons for allowance (pg. 2), the Examiner indicated that the "[p]rior art failed to establish a fin field effect transistor (FinFET) comprising a reserved T-shaped fin, wherein the reversed T-shaped fin comprises an upper portion and a lower portion, wherein the height of the upper portion ranges from 200 Angstrom to 1500 Angstrom and wherein the height of the lower portion ranges from 100 Angstrom to 1000 Angstrom, source and drain regions formed adjacent to reversed T-shaped fin, a dielectric layer formed adjacent surfaces of the fin and a gate formed adjacent the dielectric layer." This statement of reasons for allowance appears to be directed to the features of independent claim 1. Applicants note, however, that independent claim 17 recites a combination of features, which may have different scope than the features of claim 1, that is not suggested or disclosed by the reference(s) of record.

For example, independent claim 17 recites a semiconductor device that includes a fin structure including an upper portion and a lower portion, a width of the upper portion of the fin structure being smaller than a width of the lower portion of the fin structure, wherein the width of the upper portion ranges from about 100 Å to about 1000 Å and wherein the width of the lower portion ranges from about 100 Å to about 1000 Å; source and drain regions formed adjacent the fin structure; a dielectric layer formed over the fin structure; and a gate formed over the dielectric layer.

Applicants submit that it is the novel and non-obvious combination of features recited in independent claim 17 that distinguishes this claim over the reference(s) of record.

In view of the foregoing remarks, Applicants respectfully request the Examiner's reconsideration of this application, and the timely allowance of the pending claims. To the extent necessary, a petition for an extension of time under 37 CFR § 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 50-1070 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: June 22, 2007

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